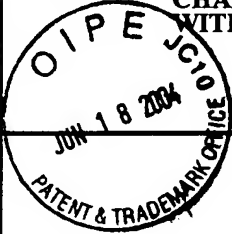


TRANSMITTAL OF FORMAL DRAWINGSDocket No.
FIS920030375US1 (17192)In Re Application Of: **Huajie Chen, et al**Serial No.
10/709,239Filing Date
April 23, 2004Confirmation No.
UnassignedExaminer
UnassignedArt Unit
UnassignedInvention: **STRUCTURES AND METHODS FOR MANUFACTURING OF DISLOCATION FREE STRESSED CHANNELS IN BULK SILICON AND SOI MOS DEVICES BY GATE STRESS ENGINEERING WITH SiGe AND/OR Si:C**Address to:
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Transmitted herewith are:

9 sheets of formal drawing(s) for this application.

☒ Each sheet of drawing indicates the identifying indicia suggested in 37 CFR Section 1.84(c).

Signature

William C. Roch
Registration No. 24,972Correspondence Address
Customer No.: 23389Dated: June 15, 2004

I certify that this document and attached formal drawings are being deposited on 6/15/04 with the U.S. Postal Service as first class mail under 37 C.F.R. 1.8 and addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

Signature of Person Mailing Correspondence**William C. Roch**

Typed or Printed Name of Person Mailing Correspondence